



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



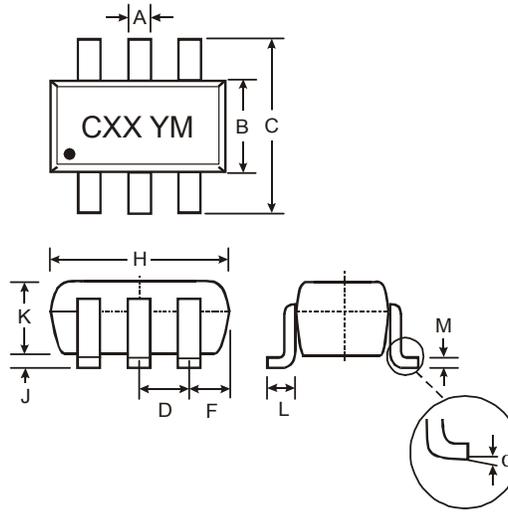
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Features

- Epitaxial Planar Die Construction
- Built-In Biasing Resistors

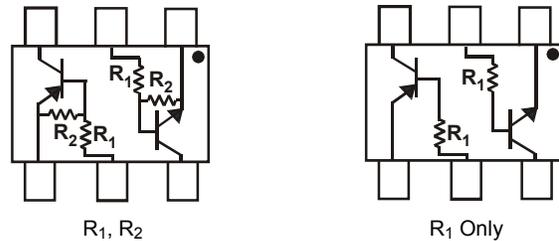
Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Type Code: See Table Below
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

P/N	R1 (NOM)	R2 (NOM)	Type Code
NK-DCX122LU	0.22K	10K	C81
NK-DCX142JU	0.47K	10K	C82
NK-DCX122TU	0.22K	OPEN	C83
NK-DCX142TU	0.47K	OPEN	C84



SCHEMATIC DIAGRAM

Maximum Ratings NPN Section

 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	-5 to +6	V
Input Voltage	$V_{EBO (MAX)}$	5	V
Output Current	I_C	100	mA
Power Dissipation	P_d	200	mW
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Maximum Ratings PNP Section

 @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	-50	V
Input Voltage	NK-DCX122LU NK-DCX142JU V _{IN}	+5 to -6 +5 to -6	V
Input Voltage	NK-DCX122TU NK-DCX142TU V _{EBO (MAX)}	-5	V
Output Current	All I _C	-100	mA
Power Dissipation	(Note 1,2) P _d	200	mW
Thermal Resistance, Junction to Ambient Air	(Note 1,2) R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics NPN Section

 @T_A = 25°C unless otherwise specified

R1, R2 Types

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	NK-DCX122LU NK-DCX142JU V _{I(off)}	0.3 0.3	—	—	V	V _{CC} = 5V, I _O = 100μA
	NK-DCX122LU NK-DCX142JU V _{I(on)}	—	—	2.0 2.0	V	V _O = 0.3V, I _O = 20mA V _O = 0.3V, I _O = 20mA
Output Voltage	V _{O(on)}	—	—	0.3V	V	I _O /I _I = 5mA/0.25mA
Input Current	NK-DCX122LU NK-DCX142JU I _I	—	—	28 13	mA	V _I = 5V
Output Current	I _{O(off)}	—	—	0.5	μA	V _{CC} = 50V, V _I = 0V
DC Current Gain	NK-DCX122LU NK-DCX142JU G _I	56 56	—	—	—	V _O = 5V, I _O = 10mA
Gain-Bandwidth Product*	f _T	—	200	—	MHZ	V _{CE} = 10V, I _E = 5mA, f = 100MHZ

* Transistor - For Reference Only

Electrical Characteristics NPN Section

 @T_A = 25°C unless otherwise specified

R1 Only

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CB0}	50	—	—	V	I _C = 50μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	40	—	—	V	I _C = 1mA
Emitter-Base Breakdown Voltage	NK-DCX122TU NK-DCX142TU BV _{EBO}	5	—	—	V	I _E = 50μA I _E = 50μA
Collector Cutoff Current	I _{CBO}	—	—	0.5	μA	V _{CB} = 50V
Emitter Cutoff Current	NK-DCX122TU NK-DCX142TU I _{EBO}	— —	— —	0.5 0.5	μA	V _{EB} = 4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	—	0.3	V	I _C = 5mA, I _B = 0.25mA
DC Current Transfer Ratio	NK-DCX122TU NK-DCX142TU h _{FE}	100 100	250 250	600 600	—	I _C = 1mA, V _{CE} = 5V
Gain-Bandwidth Product*	f _T	—	200	—	MHZ	V _{CE} = 10V, I _E = -5mA, f = 100MHZ

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Electrical Characteristics PNP Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified **R1, R2 Types**

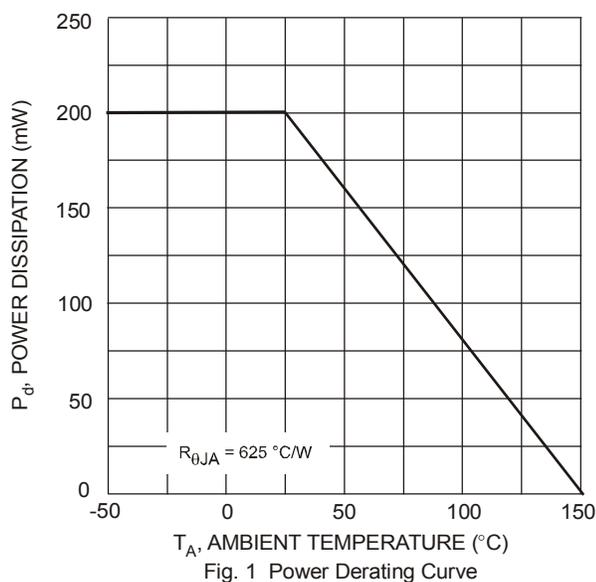
Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	NK-DCX122LU NK-DCX142JU	$V_{I(off)}$	-0.3 -0.3	—	—	V	$V_{CC} = -5V, I_O = -100\mu A$
	NK-DCX122LU NK-DCX142JU	$V_{I(on)}$	—	—	-2.0 -2.0	V	$V_O = -0.3V, I_O = -20mA$ $V_O = -0.3V, I_O = -20mA$
Output Voltage		$V_{O(on)}$	—	—	-0.3V	V	$I_O/I_I = -5mA/-0.25mA$
Input Current	NK-DCX122LU NK-DCX142JU	I_I	—	—	-28 -13	mA	$V_I = -5V$
Output Current		$I_{O(off)}$	—	—	-0.5	μA	$V_{CC} = -50V, V_I = 0V$
DC Current Gain	NK-DCX122LU NK-DCX142JU	G_I	56 56	—	—	—	$V_O = -5V, I_O = -10mA$
Gain-Bandwidth Product*		f_T	—	200	—	MHz	$V_{CE} = -10V, I_E = -5mA, f = 100MHz$

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Electrical Characteristics PNP Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified **R1 Only Types**

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV_{CBO}	-50	—	—	V	$I_C = -50\mu A$
Collector-Emitter Breakdown Voltage		BV_{CEO}	-40	—	—	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	NK-DCX122TU NK-DCX142TU	BV_{EBO}	-5	—	—	V	$I_E = -50\mu A$ $I_E = -50\mu A$
Collector Cutoff Current		I_{CBO}	—	—	-0.5	μA	$V_{CB} = -50V$
Emitter Cutoff Current	NK-DCX122TU NK-DCX142TU	I_{EBO}	—	—	-0.5 -0.5	μA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	—	—	-0.3	V	$I_C = -5mA, I_B = -0.25mA$
DC Current Transfer Ratio	NK-DCX122TU NK-DCX142TU	h_{FE}	100 100	250 250	600 600	—	$I_C = -1mA, V_{CE} = -5V$
Gain-Bandwidth Product*		f_T	—	200	—	MHz	$V_{CE} = -10V, I_E = 5mA, f = 100MHz$

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(150mW per element must not be exceeded).